# Small Signal MOSFET

-20 V, -180 mA, Dual P-Channel, 1.0 x 1.0 mm SOT-963 Package

#### **Features**

- Dual P-Channel MOSFET
- Offers a Low R<sub>DS(ON)</sub> Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics.
- These are Pb-Free Devices

#### **Applications**

- General Purpose Interfacing Switch
- Optimized for Power Management in Ultra Portable Equipment

#### MAXIMUM RATINGS (T<sub>.1</sub> = 25°C unless otherwise specified)

Para	Symbol	Value	Unit			
Drain-to-Source Voltag	V <sub>DSS</sub>	-20	V			
Gate-to-Source Voltag	е		V <sub>GS</sub>	±8	V	
Continuous Drain	Steady	$T_A = 25^{\circ}C$		-140		
Current (Note 1)	State	$T_A = 85^{\circ}C$	Ι <sub>D</sub>	-100	mA	
	t ≤ 5 s	$T_A = 25^{\circ}C$		-180		
Power Dissipation	Steady State	T <sub>A</sub> = 25°C	P <sub>D</sub>	-125		
(Note 1)					mW	
	t ≤ 5 s			-200		
Pulsed Drain Current	I <sub>DM</sub>	-600	mA			
Operating Junction and	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C			
Source Current (Body I	I <sub>S</sub>	-200	mA			
Lead Temperature for S (1/8" from case for 1	ΤL	260	°C			

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

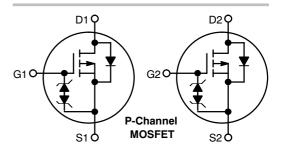
2. Pulse Test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%

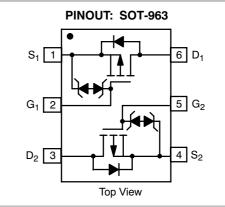


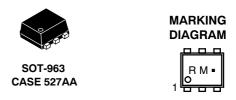
## **ON Semiconductor®**

#### http://onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> Max
-20 V	5.0 Ω @ -4.5 V	
	7.0 Ω @ -2.5 V	-0.18 A
	10 Ω @ -1.8 V	-0.16 A
	14 Ω @ -1.5 V	







- R = Specific Device Code Μ
  - = Date Code
  - = Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

#### THERMAL RESISTANCE RATINGS

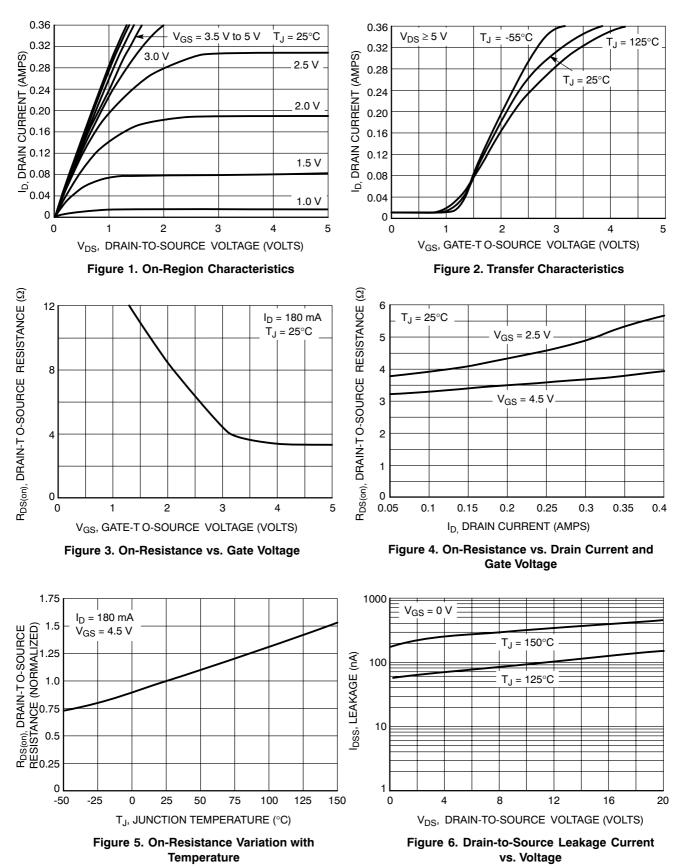
Parameter	Symbol	Мах	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{ hetaJA}$	1000	°C/W
Junction-to-Ambient – t = 5 s (Note 3)		600	

3. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

#### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS		•		•	•	. 1	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 V, I_D = -2$	250 μA	-20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = -5.0 V	$T_J = 25^{\circ}C$			-50	nA
			T <sub>J</sub> = 85°C			-200	
		$V_{GS}$ = 0 V, $V_{DS}$ = -16 V	T <sub>J</sub> = 25°C			-100	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ =	±5.0 V			±100	nA
ON CHARACTERISTICS (Note 4)	•	•					
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D = -2$	250 μΑ	-0.4		-1.0	V
Drain-to-Source On Resistance	R <sub>DS(ON)</sub>	$V_{GS} = -4.5 \text{ V}, \text{ I}_{\text{D}} = -100 \text{ mA}$			4.0	5.0	
		$V_{GS}$ = -2.5 V, I <sub>D</sub> = -50 mA			5.0	7.0	Ω
		$V_{GS}$ = -1.8 V, I <sub>D</sub> = -20 mA			6.5	10	
		$V_{GS} = -1.5 \text{ V}, I_D = -10 \text{ mA}$			7.5	14	
		$V_{GS}$ = -1.2 V, I <sub>D</sub> = -1.0 mA			11.5		
Forward Transconductance	<b>9</b> FS	$V_{DS}$ = -5.0 V, I <sub>D</sub> = -125 mA			0.26		S
Source-Drain Diode Voltage	V <sub>SD</sub>	$V_{GS} = 0 V, I_D = -10 mA$			-0.65	-1.0	V
CHARGES, CAPACITANCES AND GATE	RESISTANCE			-	-		
Input Capacitance	C <sub>ISS</sub>	f = 1 MHz, V <sub>GS</sub> = 0 V V <sub>DS</sub> = -15 V			12		pF
Output Capacitance	C <sub>OSS</sub>				2.7		
Reverse Transfer Capacitance	C <sub>RSS</sub>				1.0		
SWITCHING CHARACTERISTICS, V <sub>GS</sub> =	= 4.5 V (Note 4)						
Turn-On Delay Time	t <sub>d(ON)</sub>				20		
Rise Time	t <sub>r</sub>	$V_{GS}$ = -4.5 V, $V_{DD}$ = -15 V, I <sub>D</sub> = -180 mA, R <sub>G</sub> = 2.0 $\Omega$			37		ns
Turn-Of f Delay Time	t <sub>d(OFF)</sub>				112		
Fall Time	t <sub>f</sub>				97		

4. Switching characteristics are independent of operating junction temperatures



#### **TYPICAL PERFORMANCE CURVES**



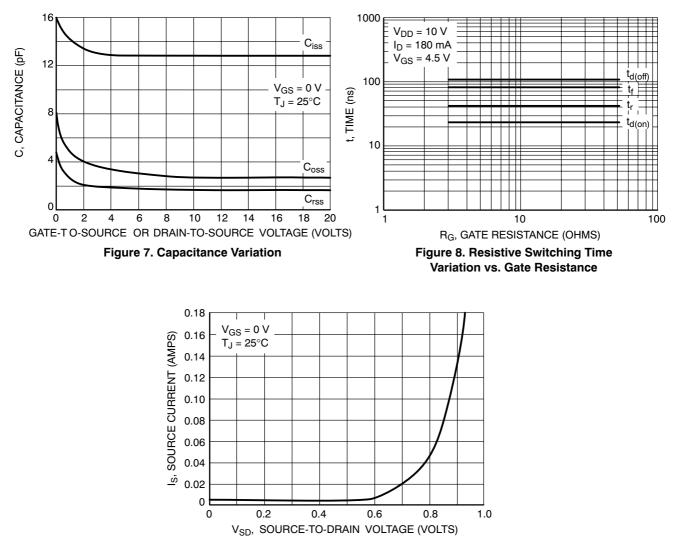


Figure 9. Diode Forward Voltage vs. Current

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
NTUD3129PT5G	SOT-963 (Pb-Free)	8000 / Tape & Reel	

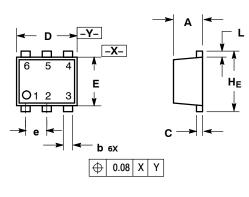
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# semi

SCALE 4:1

SOT-963 CASE 527AA **ISSUE D** 

DATE 30 JUL 2008



2. BASE 1 3. COLLECTOR 2 4. EMITTER 2 5. BASE 2 6. COLLECTOR 1	4. COLLECTOR 2 5. BASE 1 6. COLLECTOR 1	5. CATHODE 2
	2. CATHODE 3. ANODE 4. ANODE 5. CATHODE 6. CATHODE	STYLE 6: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 7: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. ANODE 6. CATHODE	STYLE 8: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 9: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1
STYLE 10: PIN 1. CATHODE 1 2. N/C 3. CATHODE 2 4. ANODE 2 5. N/C 6. ANODE 1		

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI

Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETERS MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS 2. З.

IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.40	0.45	0.50	0.016	0.018	0.020
b	0.10	0.15	0.20	0.004	0.006	0.008
С	0.05	0.10	0.15	0.002	0.004	0.006
D	0.95	1.00	1.05	0.037	0.039	0.041
Е	0.75	0.80	0.85	0.03	0.032	0.034
е	0.35 BSC		(	).014 BS	C	
L	0.05	0.10	0.15	0.002	0.004	0.006
ΗE	0.95	1.00	1.05	0.037	0.039	0.041

#### GENERIC **MARKING DIAGRAM\***

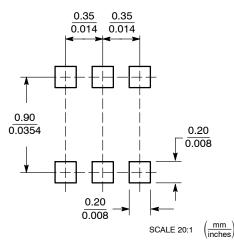


Х = Specific Device Code = Month Code Μ

\*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " .",

# may or may not be present. SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at <u>www.onsemi.com/support/sales</u>